



ON Semiconductor®

# BAV99

## 200 mA 70 V High Conductance Ultra-Fast Switching Diode

### Features

- High Conductance:  $I_F = 200 \text{ mA}$
- Fast Switching Speed:  $t_{rr} < 6 \text{ ns}$  Maximum
- Small Plastic SOT-23 Package
- Series-Pair Configuration

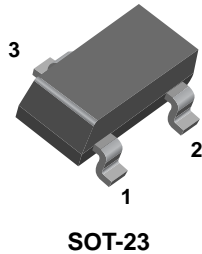
### Applications

- High-Speed Switching Applications

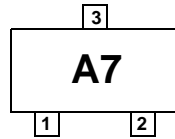
### Description

The BAV99 is a 350 mW high-speed switching diode array with series-pair diode configuration. It achieves high-current conductivity, up to 200 mA, in a very small  $7\text{mm}^2$  footprint. These features make the BAV99 optimal for area-constrained applications that need a little extra power capability.

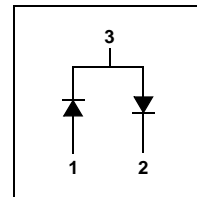
For common cathode and common anode high-speed switching diodes, explore Fairchild's BAV70 and BAW56. Looking for more options in the SOT-23 package? Check Fairchild's MMBD family.



SOT-23



### Connection Diagram



### Ordering Information

Part Number	Marking	Package	Packing Method
BAV99	A7	SOT-23 3L	Tape and Reel, Reel 7 inch
BAV99-D87Z	A7	SOT-23 3L	Tape and Reel, Reel 13 inch

## Absolute Maximum Ratings<sup>(1)</sup>

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage	70	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 Second	1.0
		Pulse Width = 300 Microseconds	8.0
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Note:

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .  
These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

## Thermal Characteristics<sup>(2)</sup>

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

### Note:

- PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

## Electrical Characteristics

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
$V_R$	Breakdown Voltage, per Diode	$I_R = 100 \mu\text{A}$	70		V
$V_F$	Forward Voltage, per Diode	$I_F = 1 \text{ mA}$		715	mV
		$I_F = 10 \text{ mA}$		855	
		$I_F = 50 \text{ mA}$		1.00	V
		$I_F = 150 \text{ mA}$		1.25	
$I_R$	Reverse Leakage, per Diode	$V_R = 70 \text{ V}$		2.5	$\mu\text{A}$
		$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$		30.0	
		$V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$		50.0	
$C_T$	Total Capacitance, per Diode	$V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$		1.5	pF
$t_{rr}$	Reverse-Recovery Time, per Diode	$I_F = I_R = 10 \text{ mA},$ $I_{RR} = 1 \text{ mA},$ $R_L = 100 \Omega$		6.0	ns

## Typical Performance Characteristics

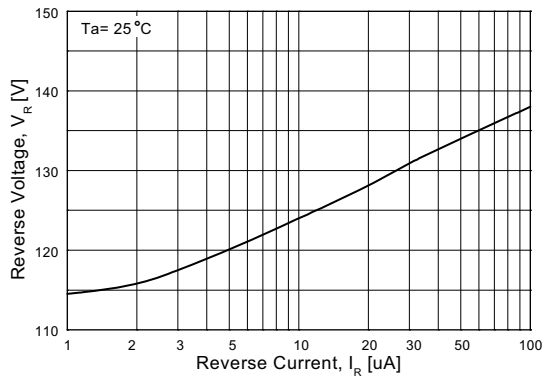


Figure 1. Reverse Voltage vs. Reverse Current

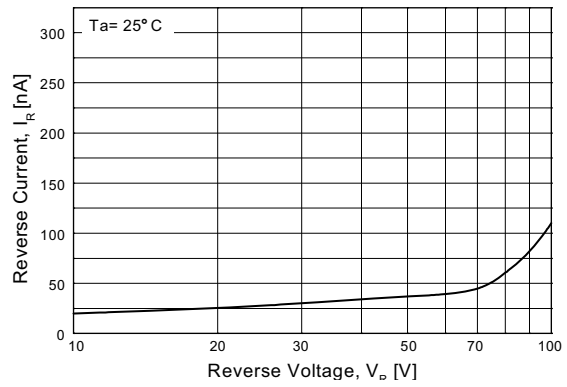


Figure 2. Reverse Current vs. Reverse Voltage

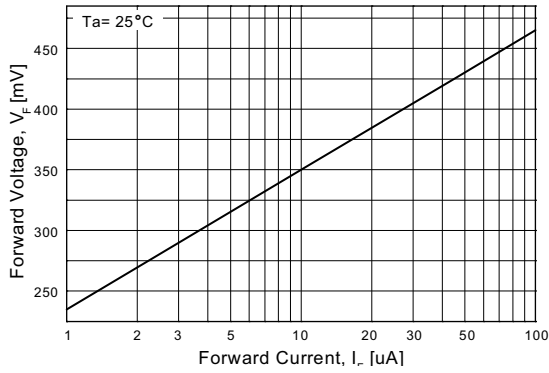


Figure 3. Forward Voltage vs. Forward Current  
 $V_F$  - 1 to 100  $\mu$ A

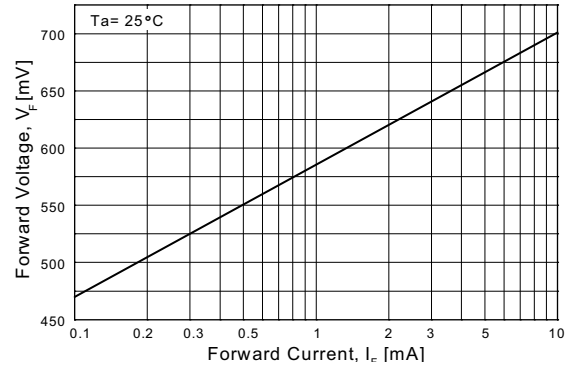


Figure 4. Forward Voltage vs. Forward Current  
 $V_F$  - 0.1 to 10 mA

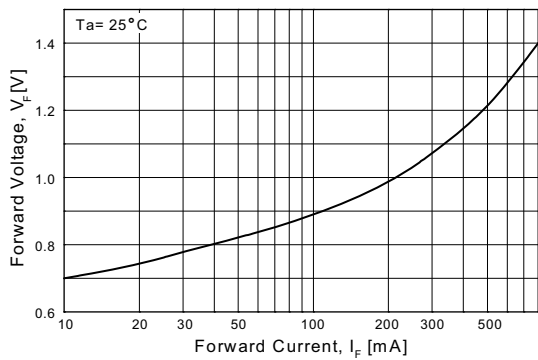


Figure 5. Forward Voltage vs. Forward Current  
 $V_F$  - 10 to 800 mA

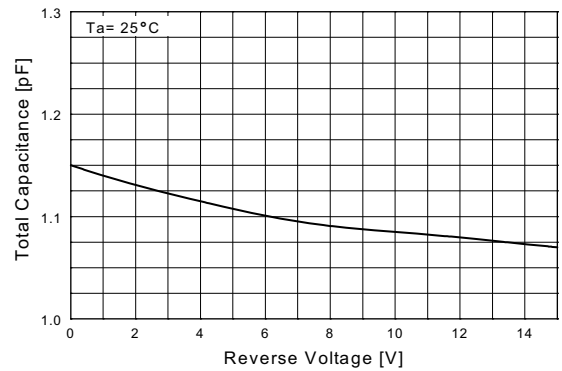
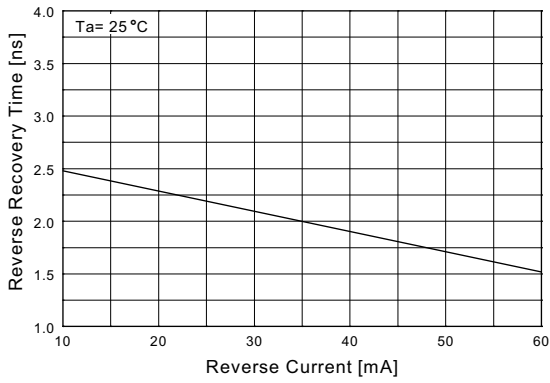
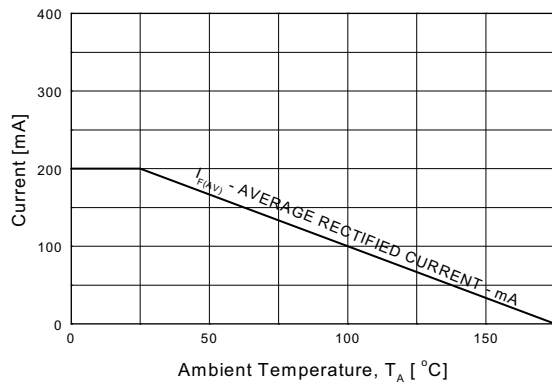


Figure 6. Total Capacitance vs. Reverse Voltage

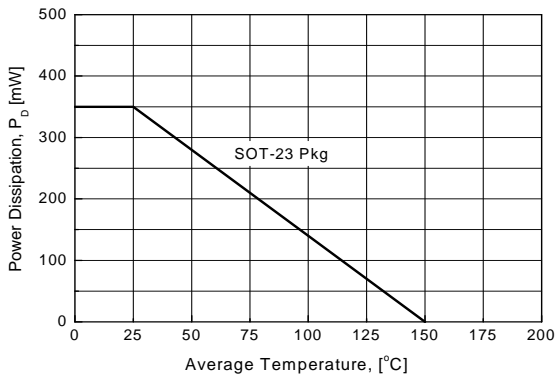
**Typical Performance Characteristics** (Continued)



**Figure 7. Reverse-Recovery Time vs. Reverse Current**



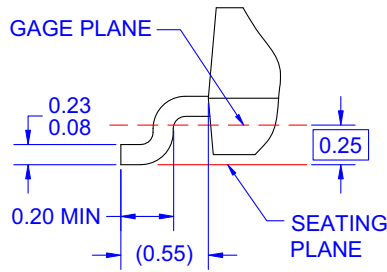
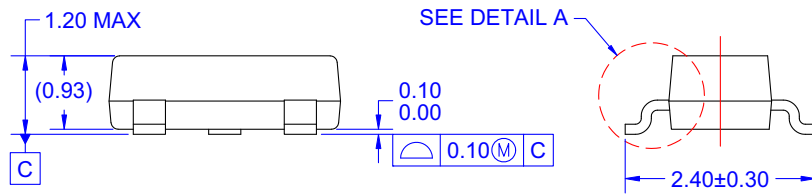
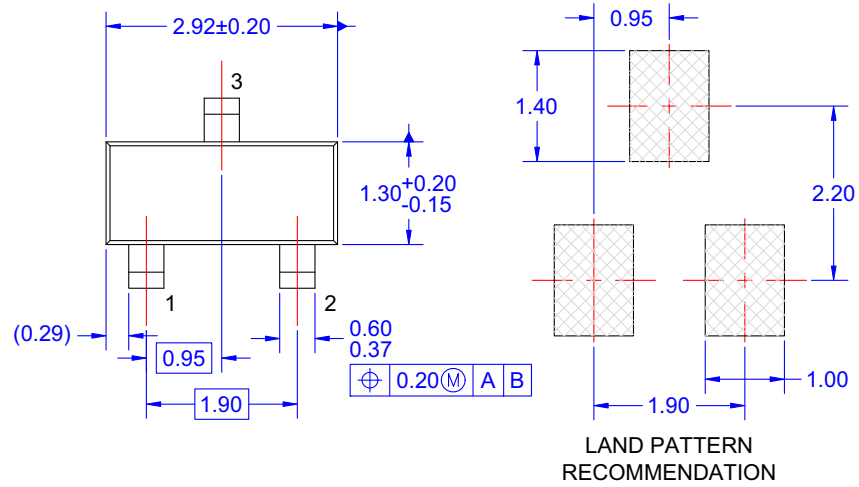
**Figure 8. Average Rectified Current ( $I_{F(AV)}$ ) vs. Ambient Temperature ( $T_A$ )**



**Figure 9. Power Derating Curve**

Physical Dimensions

SOT-23



**DETAIL A**  
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994.
- E) DRAWING FILE NAME: MA03DREV10

Figure 10. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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